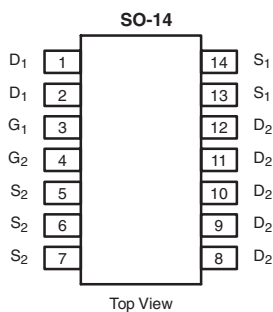


## Dual N-Channel 20-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
Channel-1	20	0.0094 at V <sub>GS</sub> = 10 V	14.1	9.6
		0.0125 at V <sub>GS</sub> = 4.5 V	12.2	
Channel-2	20	0.008 at V <sub>GS</sub> = 10 V	20	14.1
		0.0095 at V <sub>GS</sub> = 4.5 V	18.9	

SCHOTTKY PRODUCT SUMMARY		
V <sub>DS</sub> (V)	V <sub>SD</sub> (V) Diode Forward Voltage	I <sub>F</sub> (A)
20	0.55 V at 2.5 A	2



Ordering Information: Si4340CDY-T1-E3 (Lead (Pb)-free)  
Si4340CDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

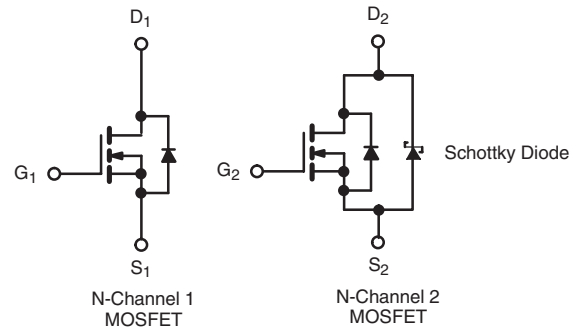
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- DC/DC Converters
  - Game Stations
  - Notebook PC Logic



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	Channel-1	Channel-2	Unit	
Drain-Source Voltage	V <sub>DS</sub>	20	20	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20	± 16		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	14.1	20	A
		T <sub>C</sub> = 70 °C	11.2	16.5	
		T <sub>A</sub> = 25 °C	11.5 <sup>b, c</sup>	15.2 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	9.2 <sup>b, c</sup>	12.2 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	40	50	A	
Source-Drain Current Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	2.5		4.5
		T <sub>A</sub> = 25 °C	1.7 <sup>b, c</sup>	2.5 <sup>b, c</sup>	
Single Pulse Avalanche Current	I <sub>AS</sub>	5		mJ	
Single Pulse Avalanche Energy	E <sub>AS</sub>	1.25			
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3	5.4	W
		T <sub>C</sub> = 70 °C	1.9	3.5	
		T <sub>A</sub> = 25 °C	2 <sup>b, c</sup>	3 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.3 <sup>b, c</sup>	1.9 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	53	62.5	35	42	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	35	42	18	23		

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions for channel 1 is 110 °C/W and channel 2 is 87 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit		
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Ch-1	20			V	
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Ch-2	20				
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1		20		mV/ $^\circ\text{C}$	
		$I_D = 25\text{ mA}$	Ch-2		22			
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1		- 5.5			
		$I_D = 25\text{ mA}$	Ch-2		- 2.5			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1		3	V	
		$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-2	0.8		2.2		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	Ch-1			100	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	Ch-2			100		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	Ch-1			1	$\mu\text{A}$	
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	Ch-2			100		
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	Ch-1			15		
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	Ch-2			10 000		
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20			A	
		$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-2	30				
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 11.5\text{ A}$	Ch-1		0.0077	0.0094	$\Omega$	
		$V_{GS} = 10\text{ V}, I_D = 15.2\text{ A}$	Ch-2		0.0065	0.008		
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-1		0.010	0.0125		
		$V_{GS} = 4.5\text{ V}, I_D = 14\text{ A}$	Ch-2		0.0075	0.0095		
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 11.5\text{ A}$	Ch-1		45		S	
		$V_{DS} = 10\text{ V}, I_D = 15.2\text{ A}$	Ch-2		73			
<b>Dynamic<sup>a</sup></b>								
Input Capacitance	$C_{iss}$	Channel-1 $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		1300		pF	
			Ch-2		1900			
Output Capacitance	$C_{oss}$		Ch-1		330			
			Ch-2		500			
Reverse Transfer Capacitance	$C_{rss}$	Channel-2 $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		150			
			Ch-2		160			
Total Gate Charge	$Q_g$		$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 11.5\text{ A}$	Ch-1		21	32	nC
				Ch-2		31	47	
		$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 11.5\text{ A}$	Ch-1		9.6	15		
			Ch-2		14.1	22		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 11.5\text{ A}$	Ch-1		4			
Ch-2			5					
Gate-Drain Charge	$Q_{gd}$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 15.2\text{ A}$	Ch-1		3			
			Ch-2		3.5			
Gate Resistance	$R_g$		$f = 1\text{ MHz}$	Ch-1		0.65	1.2	$\Omega$
				Ch-2		1.4	2.8	

## Notes:

- a. Guaranteed by design, not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .



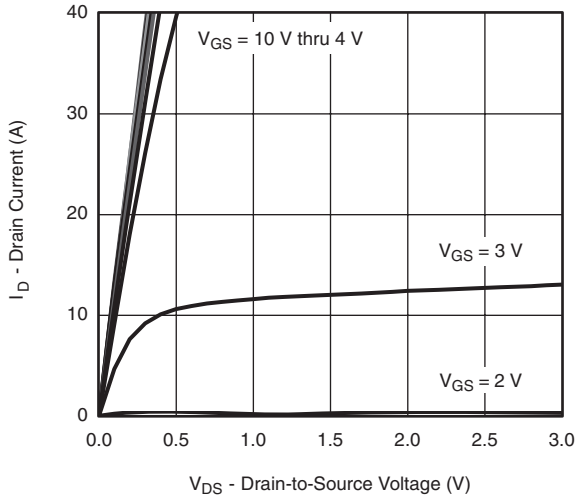
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Dynamic<sup>a</sup></b>							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 10\text{ V}$ , $R_L = 1.1\ \Omega$ $I_D \cong 9.2\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		20	30	ns
Rise Time	$t_r$		Ch-2		22	35	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 10\text{ V}$ , $R_L = 1\ \Omega$ $I_D \cong 10\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		10	15	
			Ch-2		10	15	
Fall Time	$t_f$	Channel-1 $V_{DD} = 10\text{ V}$ , $R_L = 1.1\ \Omega$ $I_D \cong 9.2\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		20	30	
			Ch-2		32	50	
Turn-On Delay Time	$t_{d(on)}$	Channel-2 $V_{DD} = 10\text{ V}$ , $R_L = 1\ \Omega$ $I_D \cong 10\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		10	15	
			Ch-2		10	15	
Rise Time	$t_r$	Channel-1 $V_{DD} = 10\text{ V}$ , $R_L = 1.1\ \Omega$ $I_D \cong 9.2\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		10	15	
			Ch-2		10	15	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 10\text{ V}$ , $R_L = 1\ \Omega$ $I_D \cong 10\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		20	30	
			Ch-2		25	40	
Fall Time	$t_f$	Channel-1 $V_{DD} = 10\text{ V}$ , $R_L = 1.1\ \Omega$ $I_D \cong 9.2\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	Ch-1		10	15	
			Ch-2		10	15	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	Ch-1			2.5	A
			Ch-2			4.5	
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$		Ch-1			40	
			Ch-2			50	
Body Diode Voltage	$V_{SD}$	$I_S = 9.2\text{ A}$ $I_S = 2.5\text{ A}$	Ch-1		0.8	1.2	V
			Ch-2		0.45	0.55	
Body Diode Reverse Recovery Time	$t_{rr}$	Channel-1 $I_F = 9.2\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	Ch-1		30	60	ns
			Ch-2		30	60	
Body Diode Reverse Recovery Charge	$Q_{rr}$	Channel-2 $I_F = 2.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	Ch-1		15	25	nC
			Ch-2		20	30	
Reverse Recovery Fall Time	$t_a$		Ch-1		12		ns
			Ch-2		14		
Reverse Recovery Rise Time	$t_b$		Ch-1		18		
			Ch-2		16		

Notes:

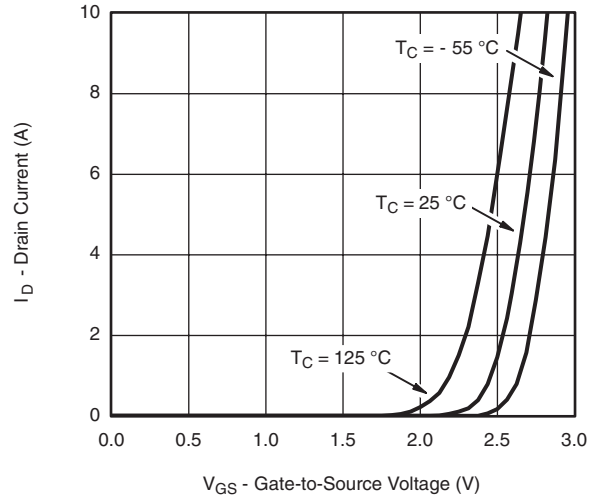
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

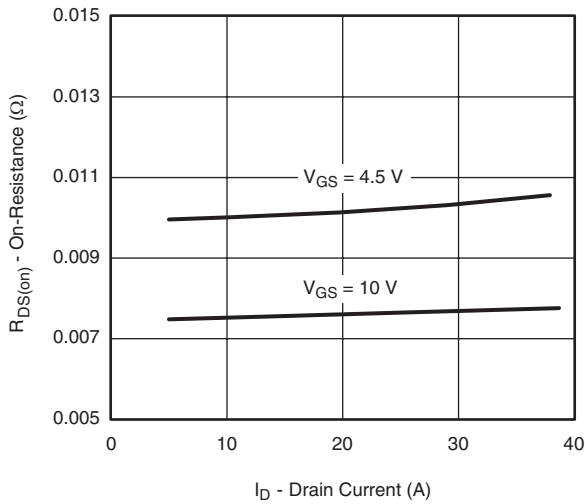
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



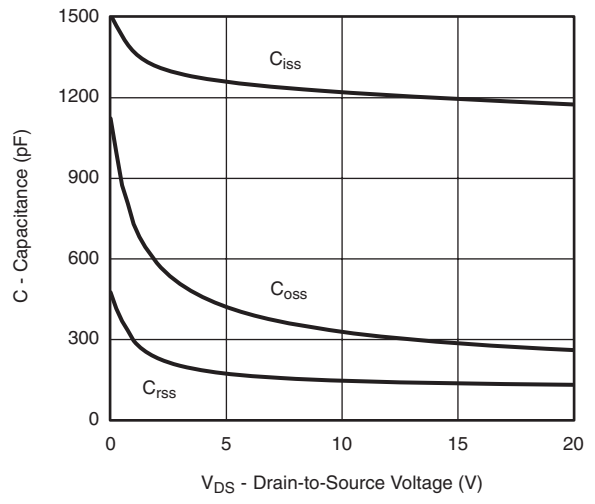
**Output Characteristics**



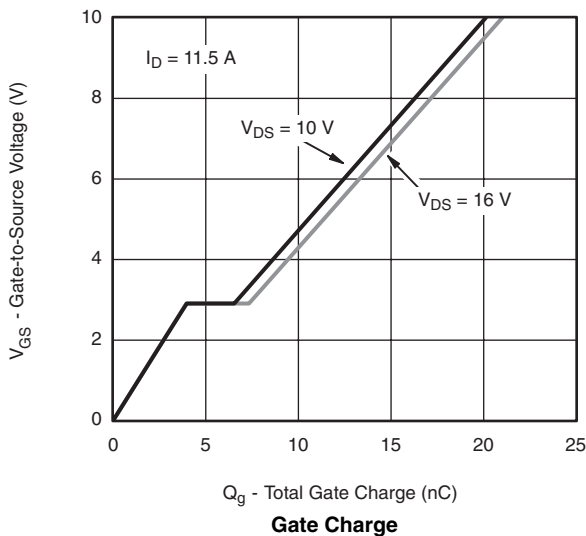
**Transfer Characteristics**



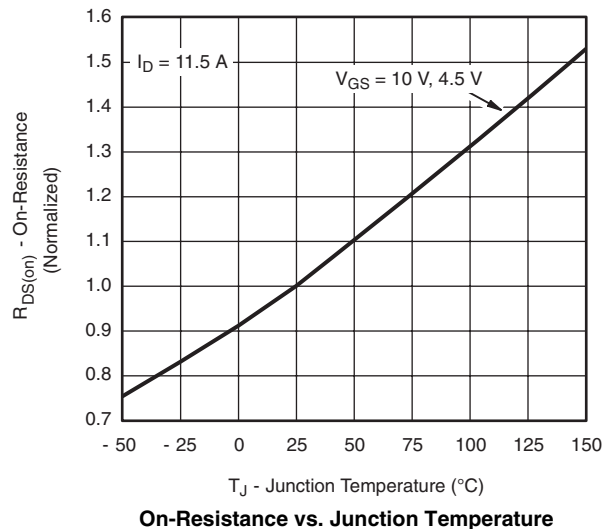
**On-Resistance vs. Drain Current**



**Capacitance**

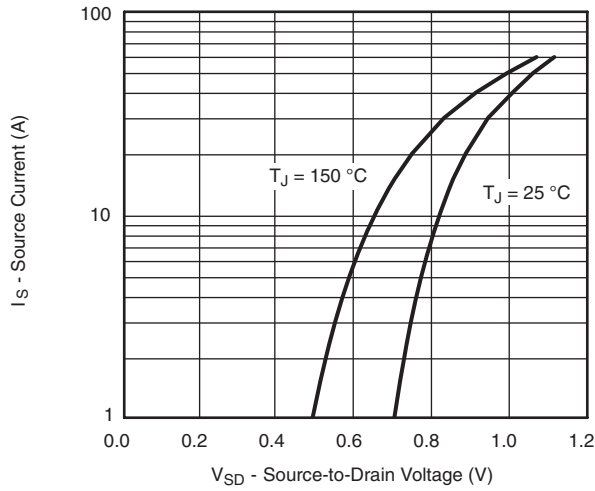


**Gate Charge**

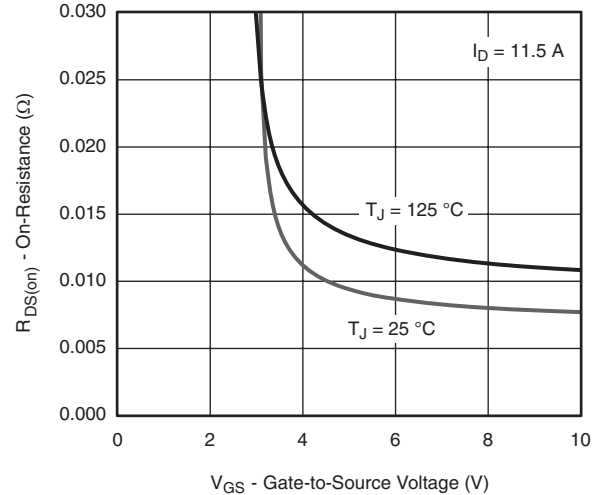


**On-Resistance vs. Junction Temperature**

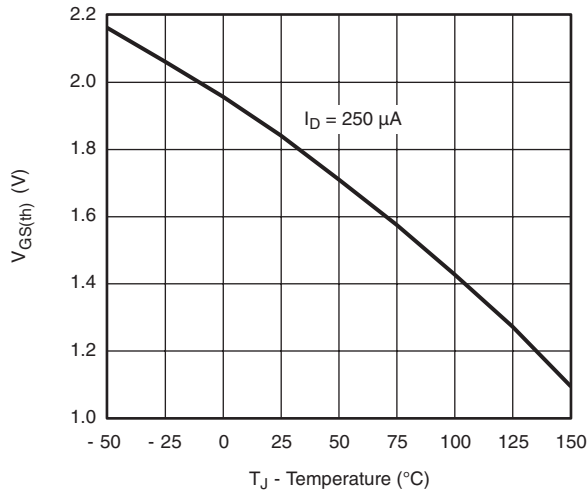
**CHANNEL-1 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



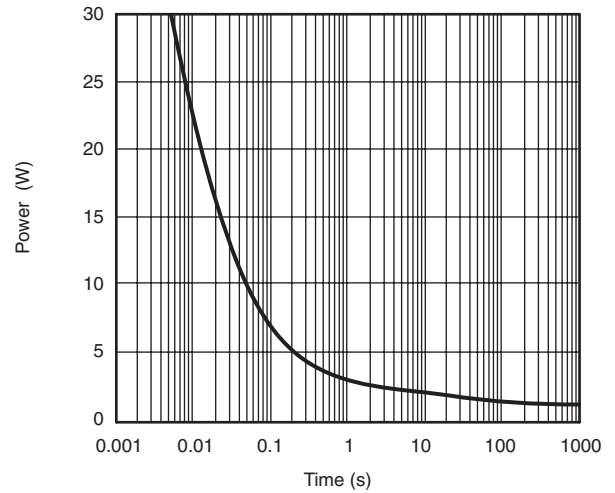
**Source-Drain Diode Forward Voltage**



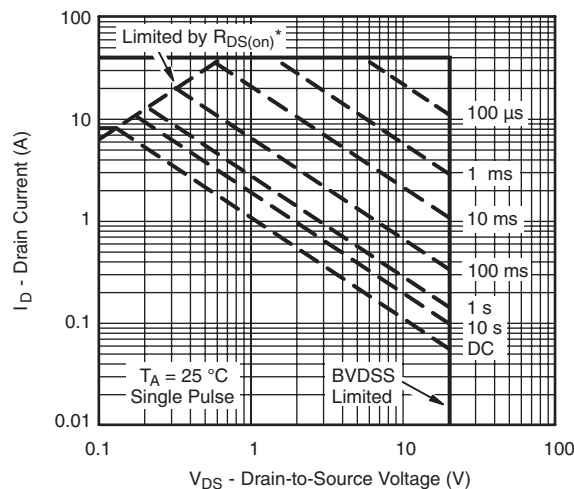
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**

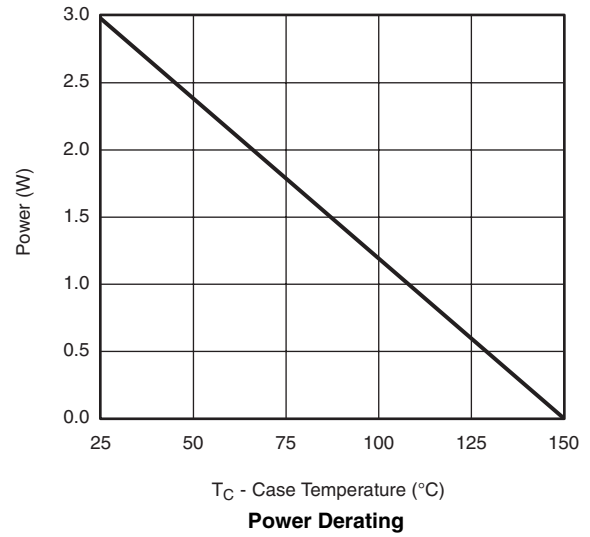
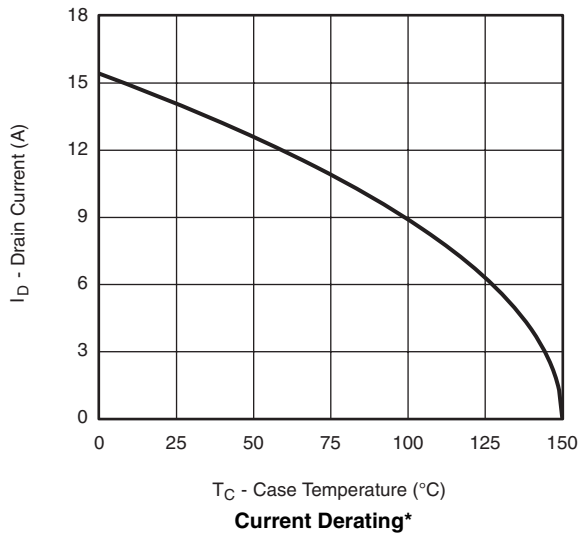


**Single Pulse Power**



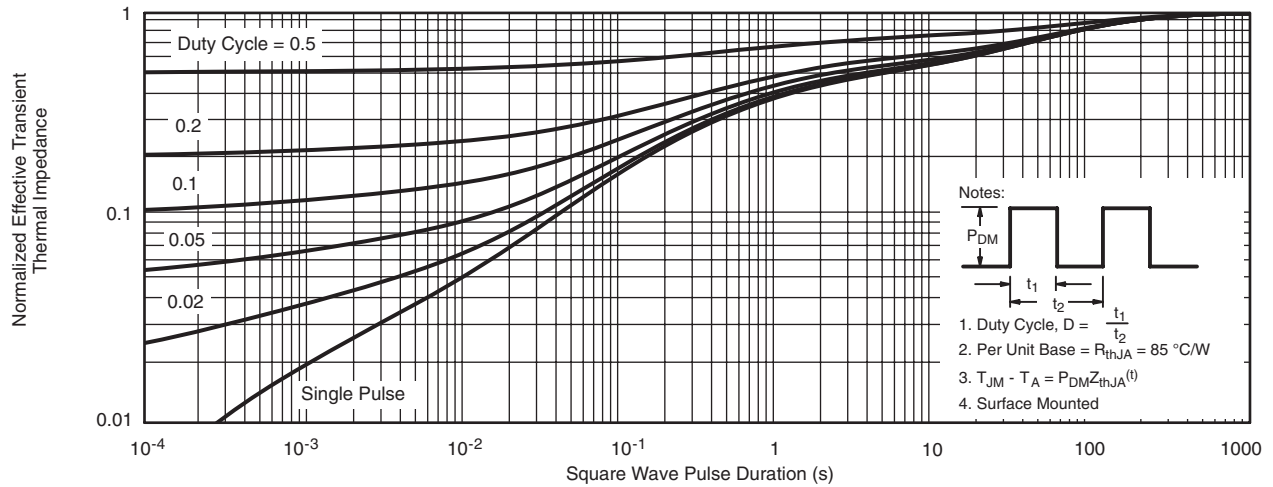
**Safe Operating Area, Junction-to-Ambient**  
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

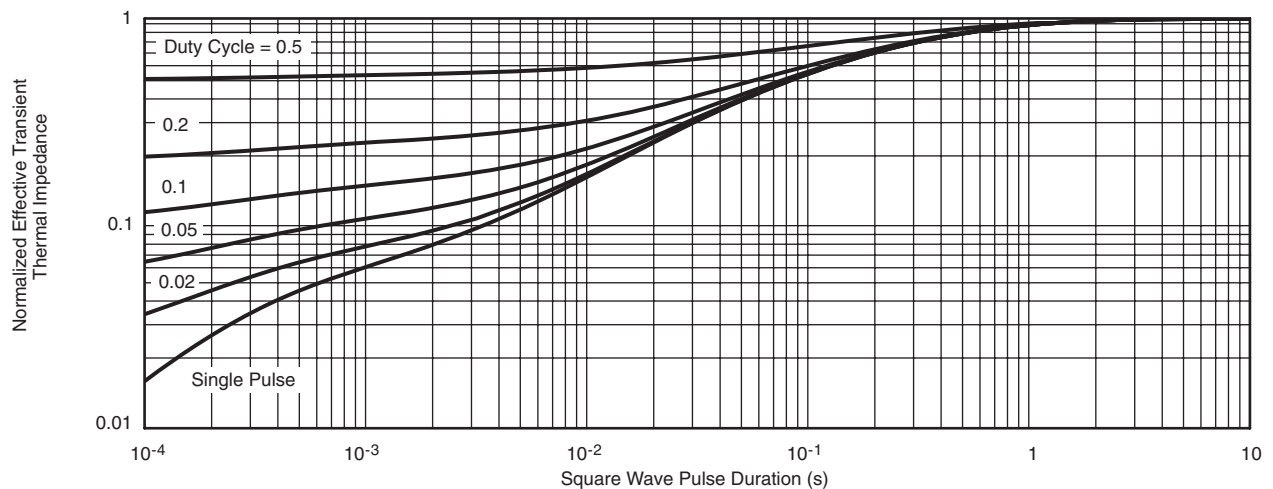


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**CHANNEL-1 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

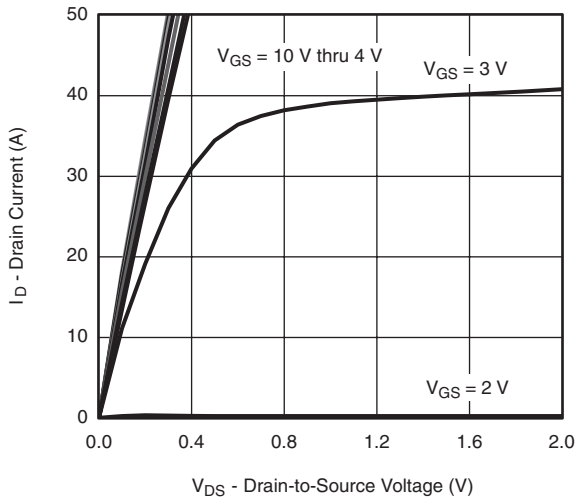


**Normalized Thermal Transient Impedance, Junction-to-Ambient**

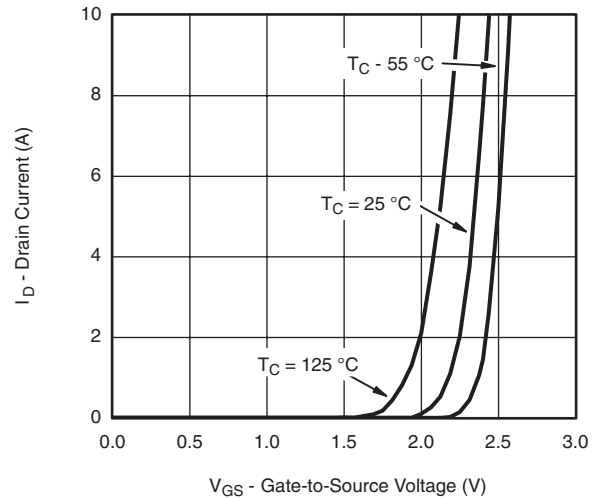


**Normalized Thermal Transient Impedance, Junction-to-Foot**

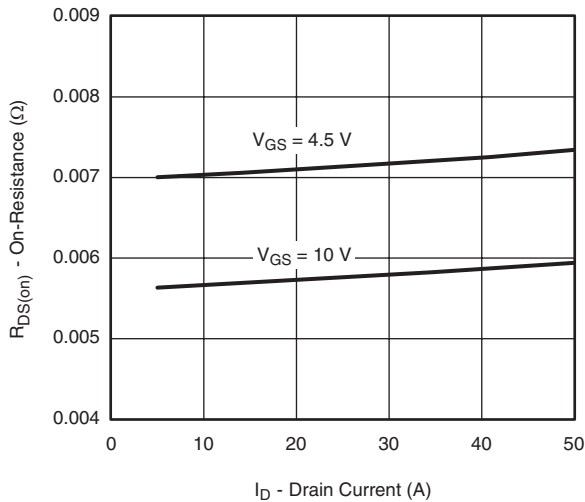
## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



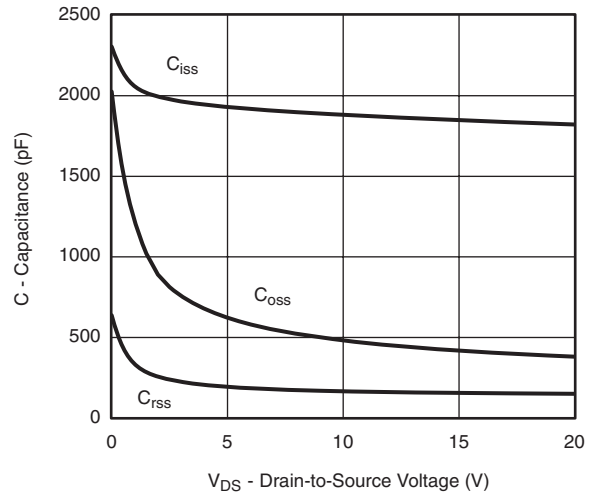
**Output Characteristics**



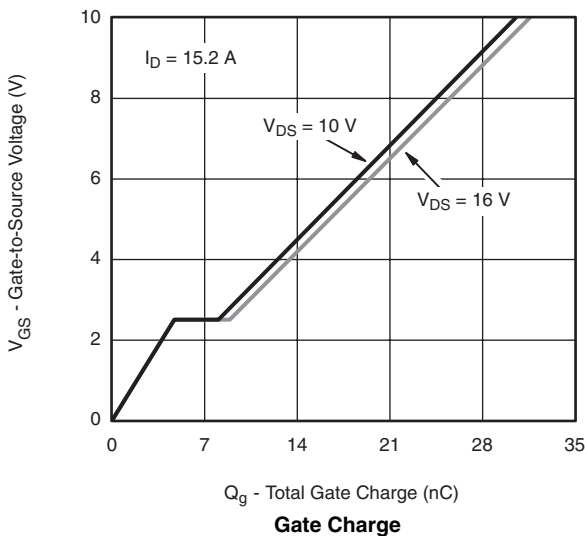
**Transfer Characteristics**



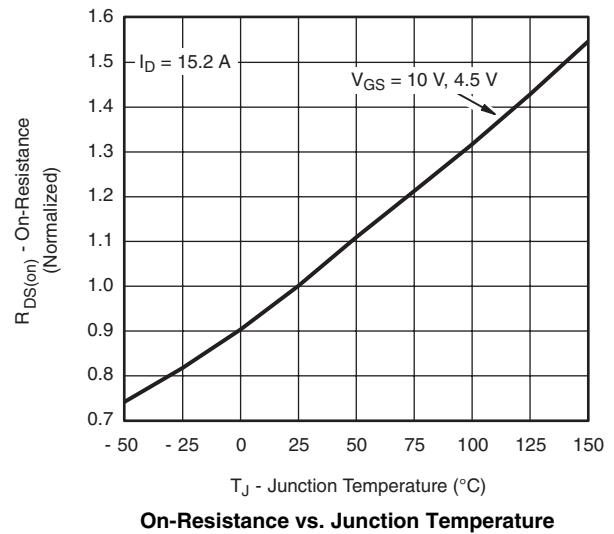
**On-Resistance vs. Drain Current**



**Capacitance**



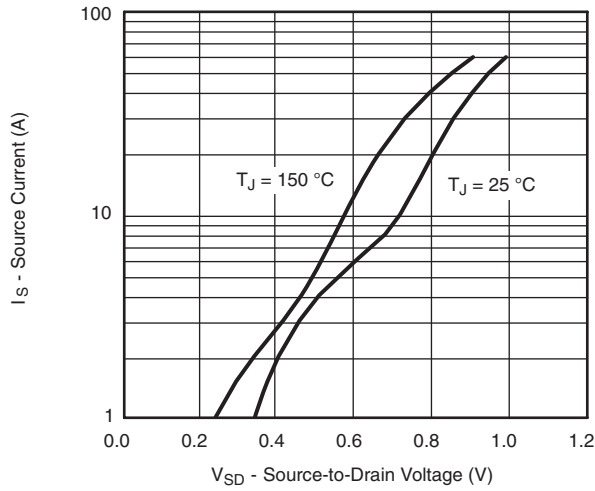
**Gate Charge**



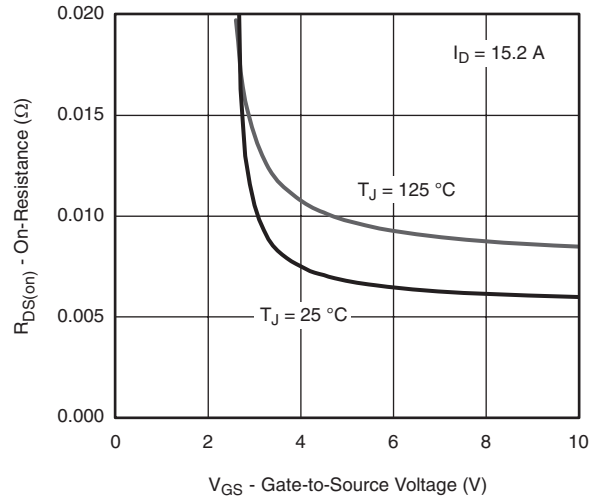
**On-Resistance vs. Junction Temperature**



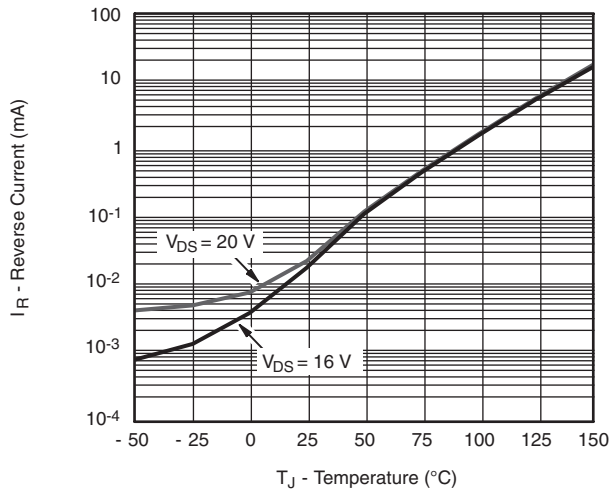
## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



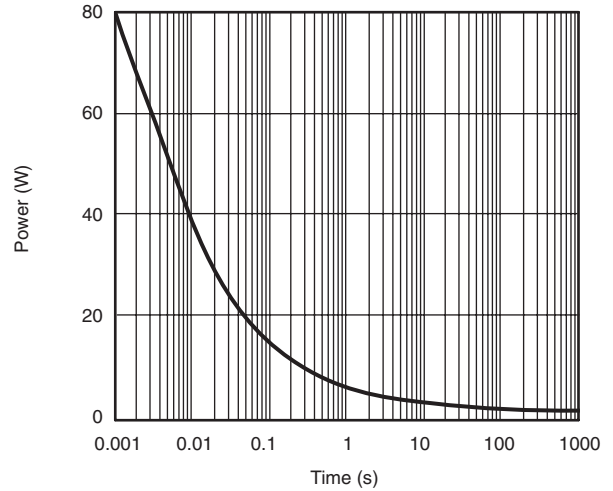
Source-Drain Diode Forward Voltage



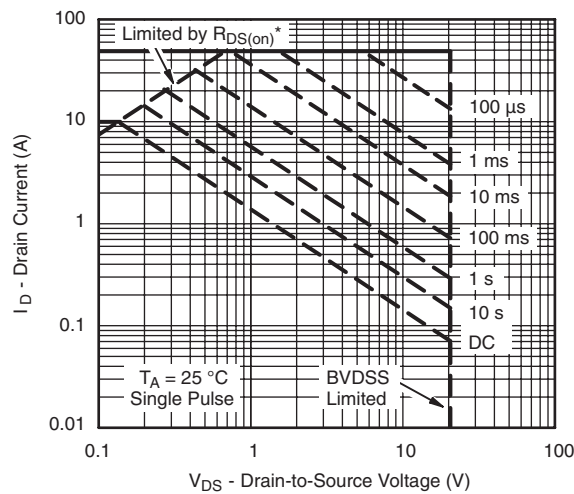
On-Resistance vs. Gate-to-Source Voltage



Reverse Current vs. Junction Temperature



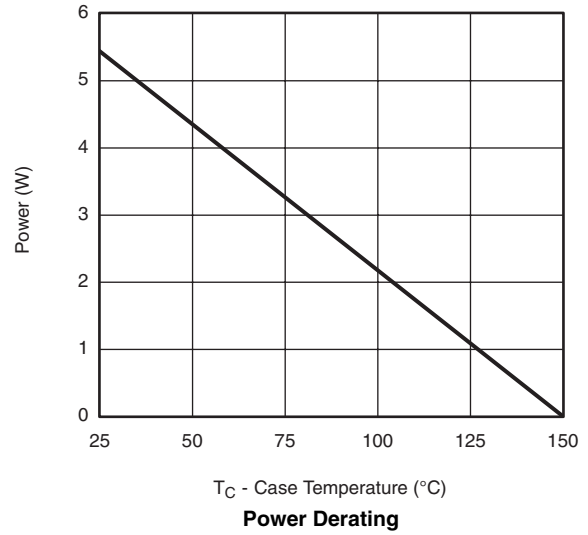
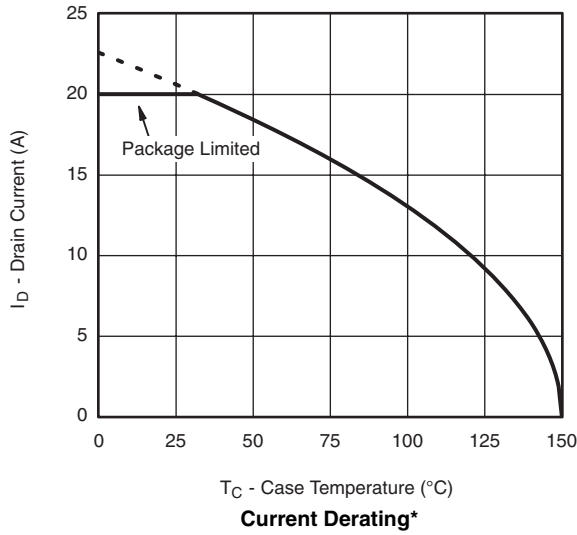
Single Pulse Power



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

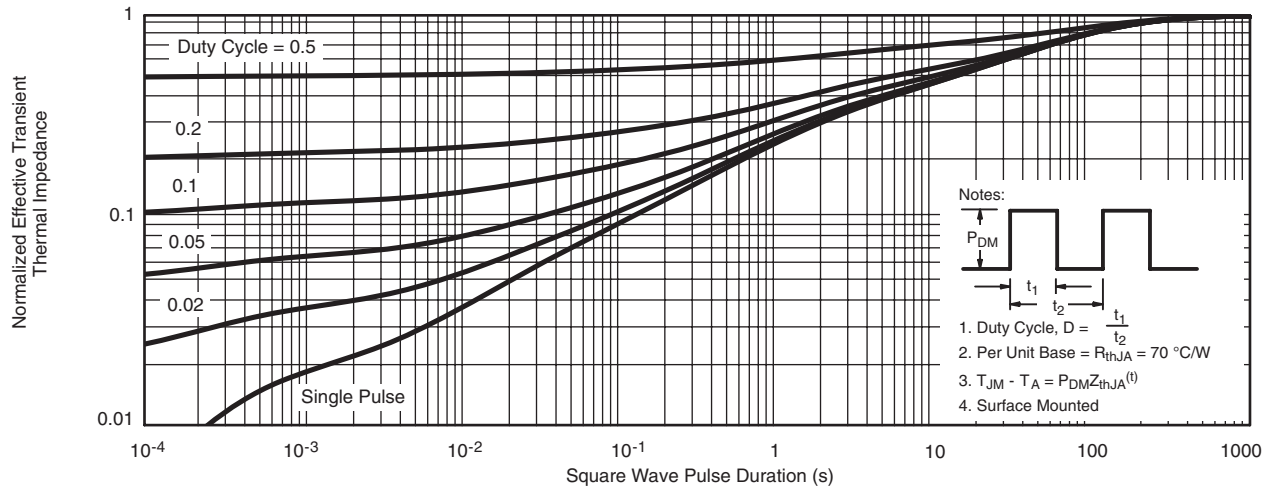
Safe Operating Area, Junction-to-Ambient

## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

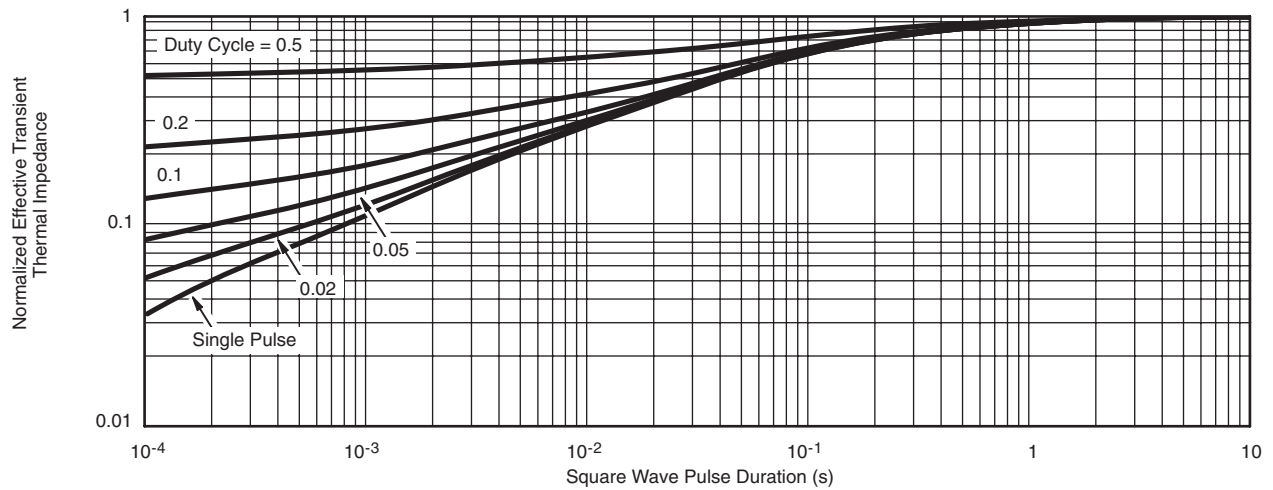


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**CHANNEL-2 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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